## **DISCRETE SEMICONDUCTORS**

# DATA SHEET

**PEMD6**; **PUMD6** NPN/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

Product data sheet Supersedes data of 2003 Nov 04 2004 Apr 07



## NPN/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

PEMD6; PUMD6

#### **FEATURES**

- Built-in bias resistors
- · Simplified circuit design
- · Reduction of component count
- · Reduced pick and place costs.

#### **APPLICATIONS**

- · Low current peripheral driver
- Replacement of general purpose transistors in digital applications
- . Control of IC inputs.

#### DESCRIPTION

NPN/PNP resistor-equipped transistors (see "\_Data\_Sheet\_Remark Supersedes data of 2003 Nov 04" for package details).

#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	_	50	V
Io	output current (DC)	_	100	mA
TR1	NPN	_	_	_
TR2	PNP	_	_	_
R1	bias resistor	4.7	_	kΩ
R2	open	_	_	_

#### **PRODUCT OVERVIEW**

TYPE NUMBER	PAC	KAGE	MARKING CODE	NPN/NPN PNP/PN		
TIPE NOMBER	PHILIPS	EIAJ	MARKING CODE	COMPLEMENT	COMPLEMENT	
PEMD6	SOT666	_	D6	PEMH7	PEMB3	
PUMD6	SOT363	SC-88	D*6 <sup>(1)</sup>	PUMH7	PUMB3	

#### Note

- 1. \* = p: Made in Hong Kong.
  - \* = t: Made in Malaysia.

#### SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING		
TTPE NUMBER	SIMPLIFIED OUTLINE AND STMBOL	PIN	DESCRIPTION	
PEMD6; PUMD6	6 5 4	1	emitter TR1	
	6   5   4	2	base TR1	
		3	collector TR2	
	TR2	4	emitter TR2	
	TR1	5	base TR2	
	1 2 3	6	collector TR1	
	1 2 3 Top view <i>MHC028</i>			

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#### **ORDERING INFORMATION**

TYPE	TYPE PACKAGE				
NUMBER	NAME DESCRIPTION VER				
PEMD6	_	plastic surface mounted package; 6 leads			
PUMD6	_	<ul> <li>plastic surface mounted package; 6 leads</li> <li>SOT36</li> </ul>			

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT		
Per transistor; for the PNP transistor with negative polarity							
V <sub>CBO</sub>	O collector-base voltage open emitter		_	50	V		
V <sub>CEO</sub>	collector-emitter voltage	open base	_	50	V		
V <sub>EBO</sub>	emitter-base voltage	open collector	_	5	V		
Io	output current (DC)		_	100	mA		
I <sub>CM</sub>	peak collector current		_	100	mA		
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1					
	SOT363	note 1	_	200	mW		
	SOT666	notes 1 and 2	_	200	mW		
T <sub>stg</sub>	storage temperature		-65	+150	°C		
Tj	junction temperature		_	150	°C		
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C		
Per device							
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1					
	SOT363	note 1	_	300	mW		
	SOT666	notes 1 and 2	_	300	mW		

#### Notes

- 1. Transistor mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

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#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transis	stor			
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient SOT363 SOT666	note 1	625 625	K/W K/W
Per device	•			
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient SOT363	note 1	416	K/W
	SOT666		416	K/W

#### Note

#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER CONDITIONS		MIN.	TYP.	MAX.	UNIT		
Per transis	Per transistor; for the PNP transistor with negative polarity							
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0	_	_	100	nA		
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0$	_	_	1	μΑ		
		$V_{CE} = 30 \text{ V}; I_{B} = 0; T_{j} = 150 ^{\circ}\text{C}$	_	_	50	μΑ		
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0	_	_	100	nA		
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 1 \text{ mA}$	200	_	_			
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}$	_	_	100	mV		
R1	input resistor		3.3	4.7	6.1	kΩ		
C <sub>c</sub>	collector capacitance	$I_E = I_e = 0$ ; $V_{CB} = 10 \text{ V}$ ; $f = 1 \text{ MHz}$						
	TR1 (NPN)		_	_	2.5	pF		
	TR2 (PNP)		_	_	3	pF		

<sup>1.</sup> Transistor mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.

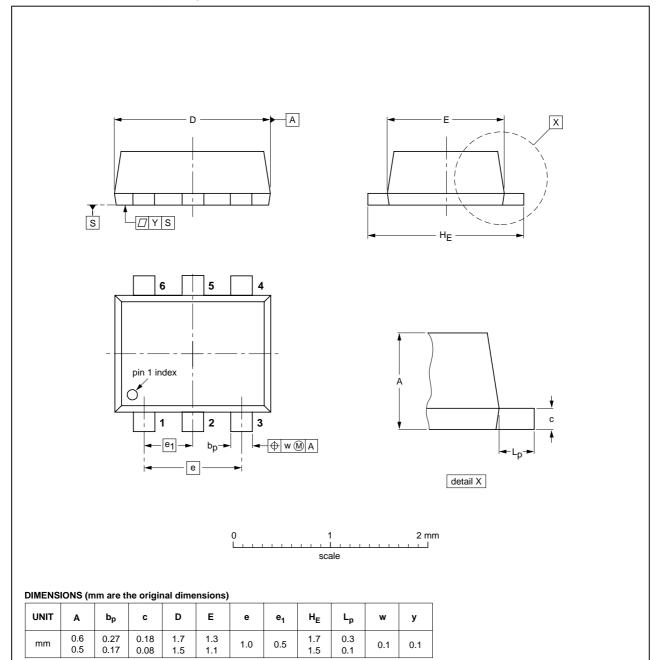
# NPN/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

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#### **PACKAGE OUTLINES**

#### Plastic surface-mounted package; 6 leads

SOT666



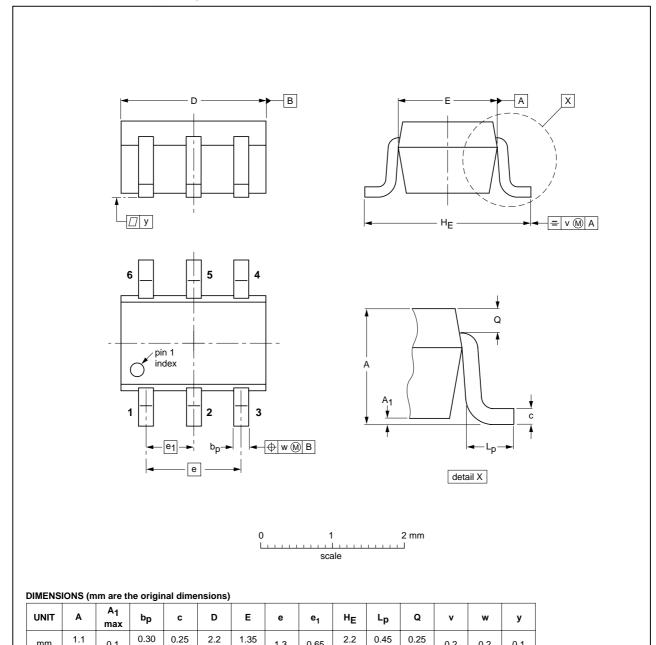
OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT666						<del>-04-11-08-</del> 06-03-16

# NPN/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

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#### Plastic surface-mounted package; 6 leads

**SOT363** 



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT363			SC-88			<del>04-11-08</del> 06-03-16

2004 Apr 07 6

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## NPN/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

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#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### **Notes**

- 1. Please consult the most recently issued document before initiating or completing a design.
- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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## **NXP Semiconductors**

#### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

#### **Contact information**

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